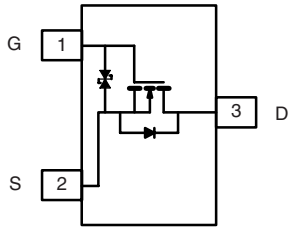
N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS(min.)}$ (V)	$R_{DS(on)}$ (Ω)	$V_{GS(th)}$ (V)	I_D (mA)
60	1.25 at V_{GS} = 10 V	1 to 2.5	330

SC-75A
(SOT-416)



Marking Code: F

Ordering Information: Si1022R-T1-E3 (Lead (Pb)-free)
Si1022R-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFETs
- Low On-Resistance: 1.25 Ω
- Low Threshold: 2.5 V
- Low Input Capacitance: 30 pF
- Fast Switching Speed: 25 ns
- Low Input and Output Leakage
- Miniature Package
- ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid State Relays

BENEFITS

- Low Offset Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Error Voltage
- Small Board Area

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current[a]	T_A = 25 °C	I_D	330	mA
	T_A = 85 °C		240	
Pulsed Drain Current[a]		I_{DM}	650	
Power Dissipation[a]	T_A = 25 °C	P_D	250	mW
	T_A = 85 °C		130	
Thermal Resistance, Maximum Junction-to-Ambient[a]		R_{thJA}	500	°C/W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

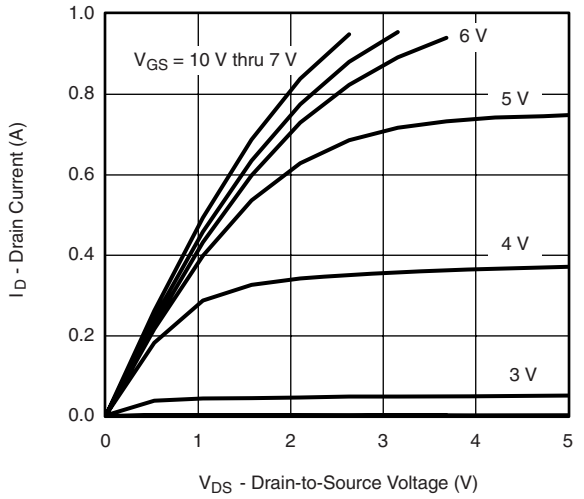
Notes:
a. Surface mounted on FR4 board, power applied for t ≤ 10 s.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 10 µA	60			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 0.25 mA	1		2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 10 V			± 150	nA
		T_J = 85 °C			± 500	
		V_{DS} = 0 V, V_{GS} = ± 5 V			± 20	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 50 V, V_{GS} = 0 V			10	
		T_J = 85 °C			100	
		V_{DS} = 60 V, V_{GS} = 0 V			1	µA
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = 10 V, V_{GS} = 4.5 V	500			mA
		V_{DS} = 7.5 V, V_{GS} = 10 V	800			
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 200 mA			3.0	Ω
		T_J = 125 °C			5.0	
		V_{GS} = 10 V, I_D = 500 mA			1.25	
		T_J = 125 °C			2.25	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 200 mA	100			mS
Diode Forward Voltage[a]	V_{SD}	V_{GS} = 0 V, I_S = 200 mA			1.3	V
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz		30		pF
Output Capacitance	C_{oss}			6		
Reverse Transfer Capacitance	C_{rss}			2.5		
Gate Charge	Q_g	V_{DS} = 10 V, I_D = 250 mA, V_{GS} = 4.5 V			0.6	nC
Switching[b, c]						
Turn-On Time	$t_{(on)}$	V_{DD} = 30 V, R_L = 150 Ω, I_D = 200 mA, V_{GEN} = 10 V, R_g = 10 Ω			25	ns
Turn-Off Time	$t_{(off)}$				35	

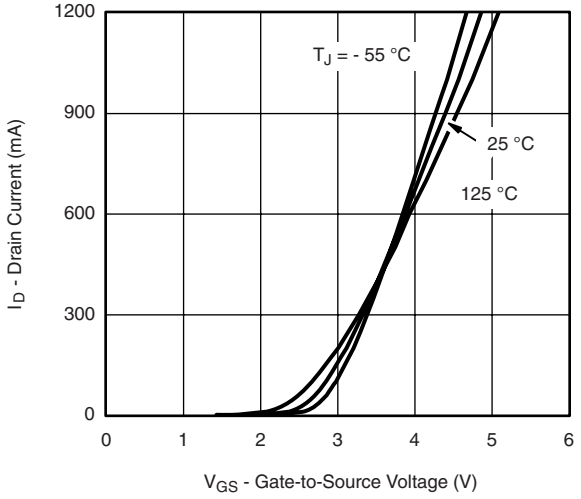
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. For DESIGN AID ONLY, not subject to production testing.
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

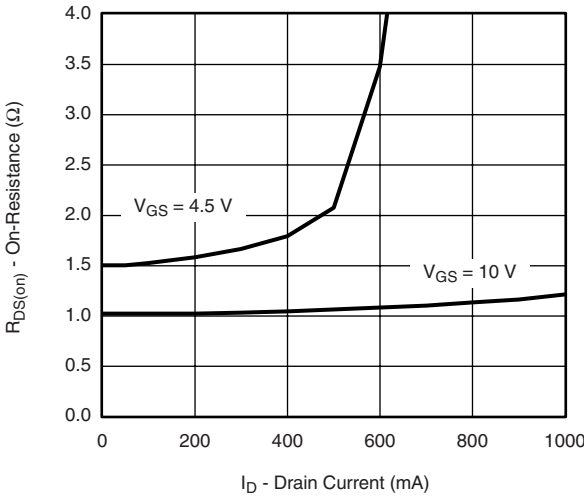
TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



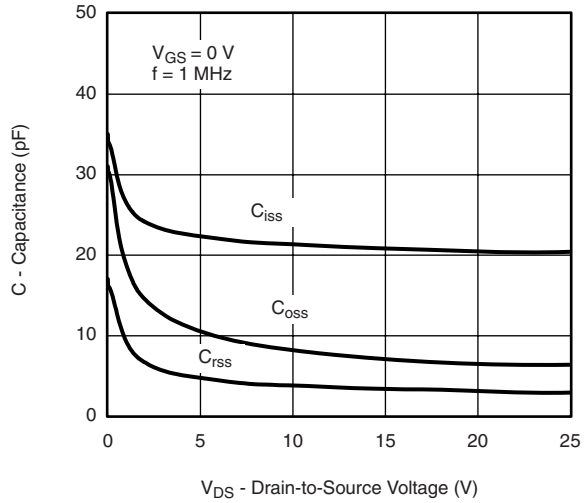
Output Characteristics



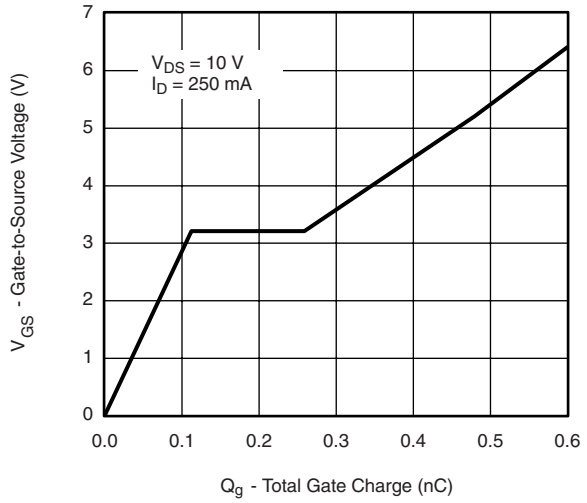
Transfer Characteristics



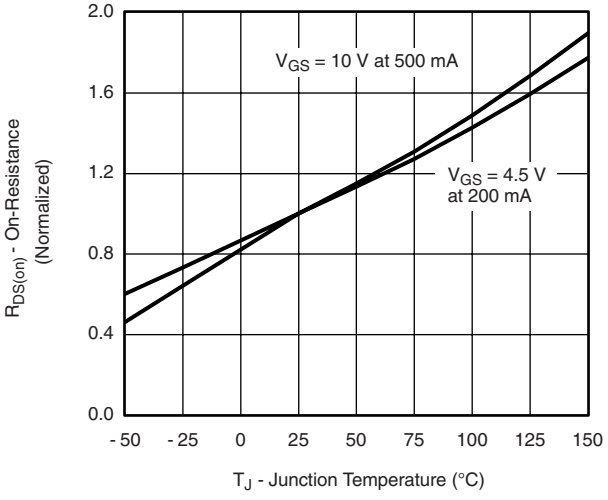
On-Resistance vs. Drain Current



Capacitance



Gate Charge



On-Resistance vs. Junction Temperature

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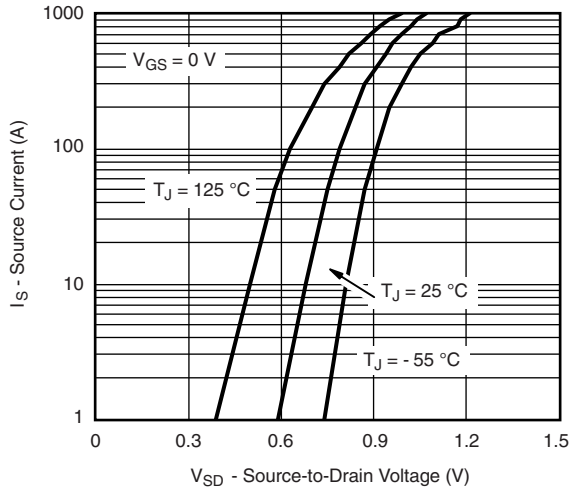
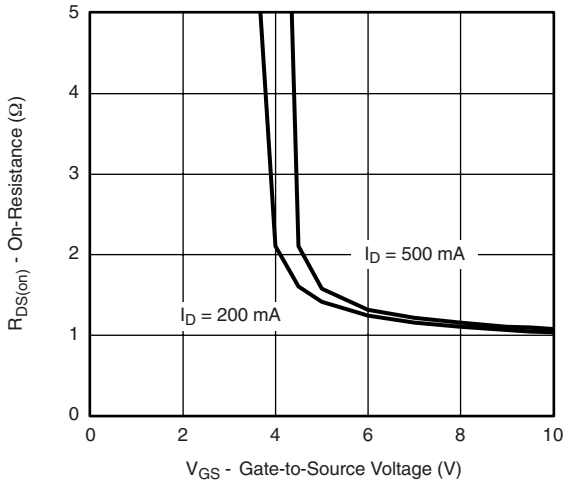
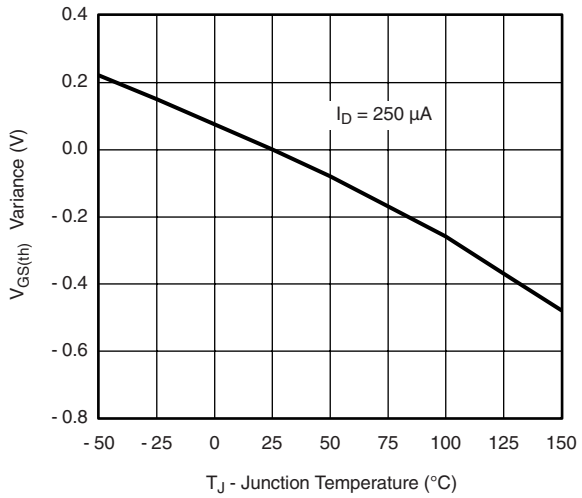


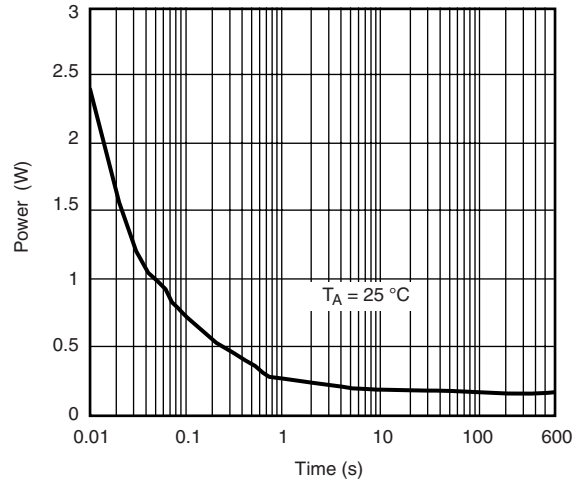
Source-Drain Diode Forward Voltage



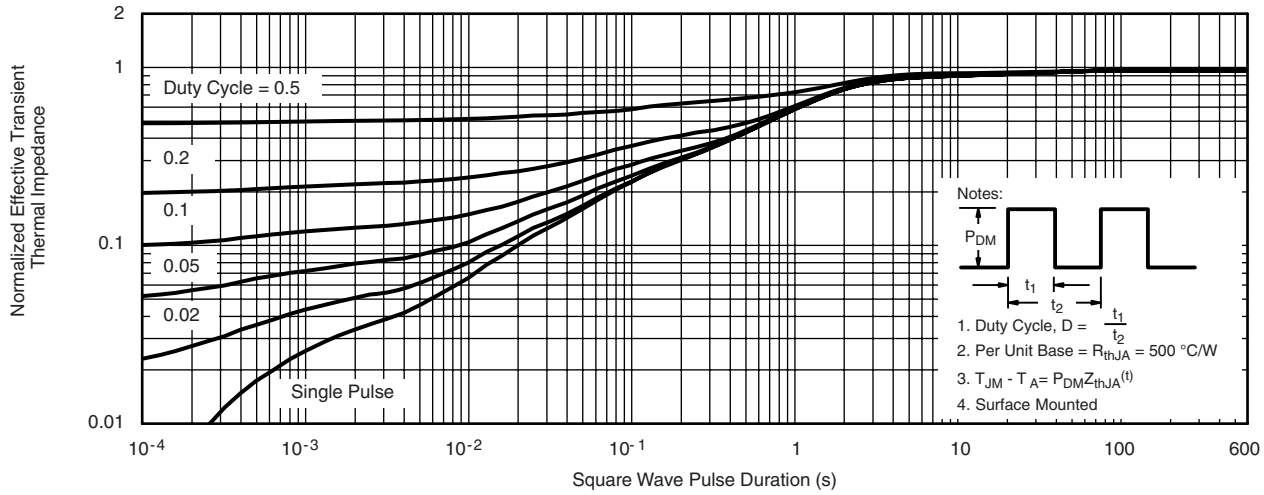
On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

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